

PUMD10-Q

NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

14 September 2021

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replaces general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor;	Per transistor; for the PNP transistor (TR2) with negative polarity, where applicable								
V _{CEO}	collector-emitter voltage	open base		-	-	50	V		
I _O	output current			-	-	100	mA		
R1	bias resistor 1		[1]	1.54	2.2	2.86	kΩ		
R2/R1	bias resistor ratio		[1]	17	21	26			

[1] See section "Test information" for resistor calculation and test conditions.



NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	01	output (collector) TR1	☐1 ☐2 ☐3 TOOODS (20T222)	
			TSSOP6 (SOT363)	GND1 I1 O2
				GND1 I1 O2 006aaa143

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PUMD10-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD10-Q	D%0

[1] % = placeholder for manufacturing site code

NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

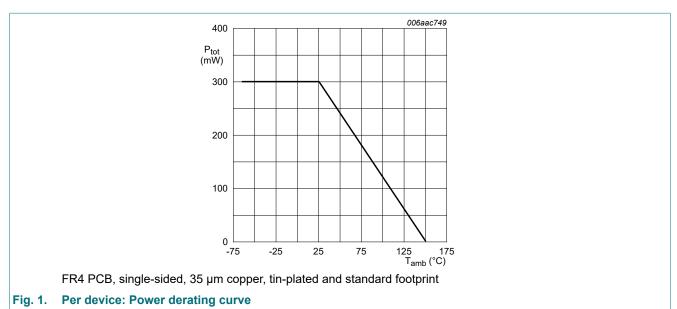
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or; for the PNP transistor (TF	(2) with negative polarity, where appl	icable	<u> </u>		
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
V _I	input voltage	positive (input voltage TR1)		-	12	V
		negative (Input voltage TR1)		-	-5	V
		positive (input voltage TR2)		-	5	V
		negative (Input voltage TR2)		-	-12	V
lo	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
Per device	<u> </u>		'	<u> </u>		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	er transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

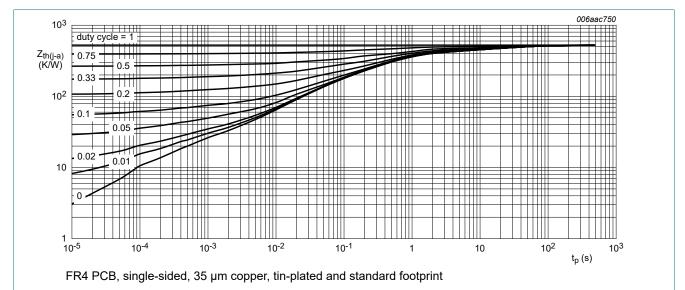


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

10. Characteristics

Table 7. Characteristics

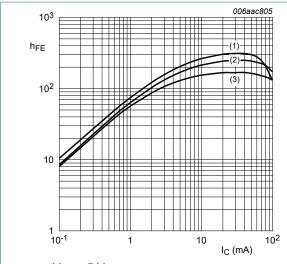
 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or; for the PNP transistor ((TR2) with negative polarity, where app	licable	•			
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 100 μA; I _E = 0 A		50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 2 mA; I _B = 0 A		50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A		-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A		-	-	100	nA
	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A		-	-	180	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 10 mA		100	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 5 mA; I _B = 0.25 mA		-	-	100	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA		-	0.6	0.5	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 5 mA		1.1	0.75	-	V
R1	bias resistor 1		[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[1]	17	21	26	
TR1 (NPN)							·
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz		-	-	2.5	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	[2]	-	230	-	MHz
TR2 (PNP)					•	•	
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz		-	-	3	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	[2]	-	180	-	MHz

^[1] See section "Test information" for resistor calculation and test conditions.

^[2] Characteristics of built-in transistor

NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω



 $V_{CE} = 5 V$ (1) $T_{amb} = 100 °C$

(2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values

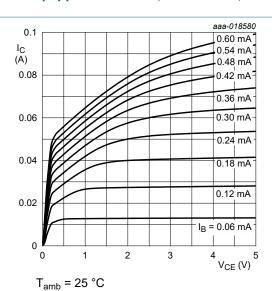
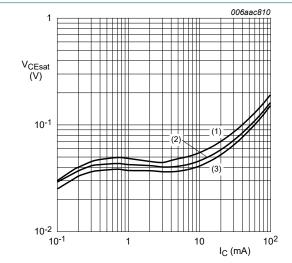


Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



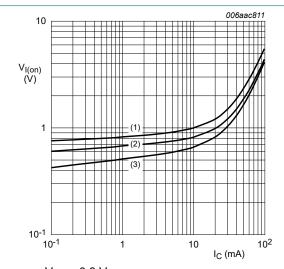
 $I_{\rm C}/I_{\rm B}=20$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) T_{amb} = -40 °C

Fig. 5. **NPN transistor: Collector-emitter saturation** voltage as a function of collector current; typical values



 $V_{CE} = 0.3 V$

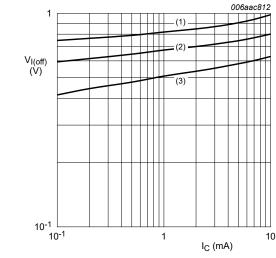
(1) $T_{amb} = -40 \, ^{\circ}C$

 $(2) T_{amb} = 25 °C$

(3) $T_{amb} = 100 \, ^{\circ}C$

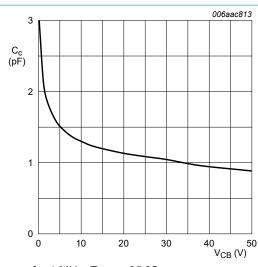
Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values

NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω



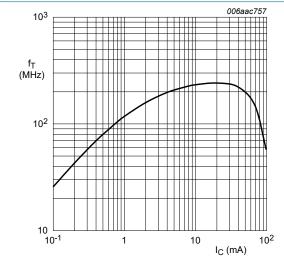
V_{CE} = 5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values



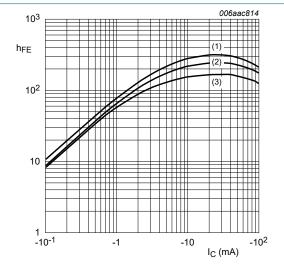
f = 1 MHz; $T_{amb} = 25 \text{ °C}$

Fig. 8. NPN transistor: Collector capacitance as a function of collector-base voltage; typical values



 V_{CE} = 5 V; T_{amb} = 25 °C

Fig. 9. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



 $V_{CE} = -5 V$

 $(1) T_{amb} = 100 °C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values

NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

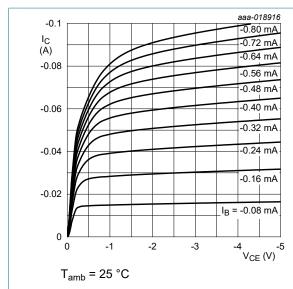
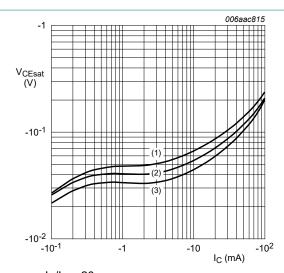
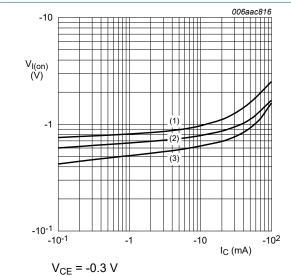


Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



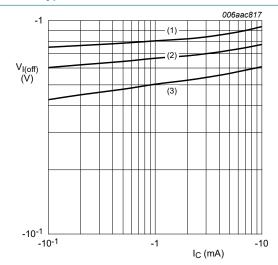
 $I_C/I_B = 20$ (1) $T_{amb} = 100 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -40 \,^{\circ}C$

Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



 $V_{CE} = -0.3 \text{ V}$ (1) $T_{amb} = -40 \text{ °C}$ (2) $T_{amb} = 25 \text{ °C}$ (3) $T_{amb} = 100 \text{ °C}$

Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values



V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values

NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

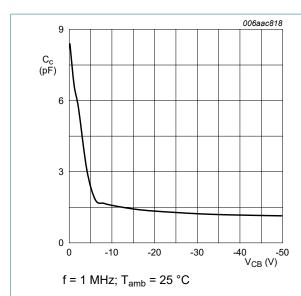


Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values

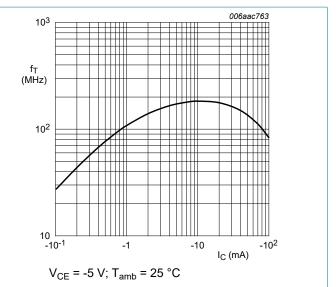


Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

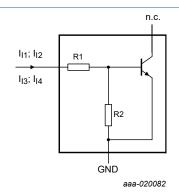


Fig. 17. NPN transistor: Resistor test circuit

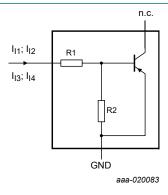


Fig. 18. PNP transistor: Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

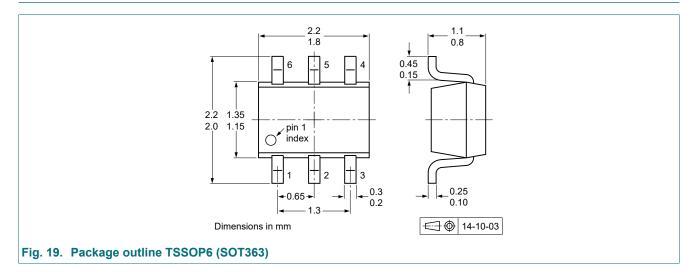
Per transistor; for the PNP transistor with reverse polarity

R1 (kΩ)	R2 (kΩ)	Test conditions	est conditions					
		I _{I1}	I ₁₂	I _{I3}	I ₁₄			
2.2	47	90 µA	140 µA	-55 μA	-105 μA			

PUMD10-Q

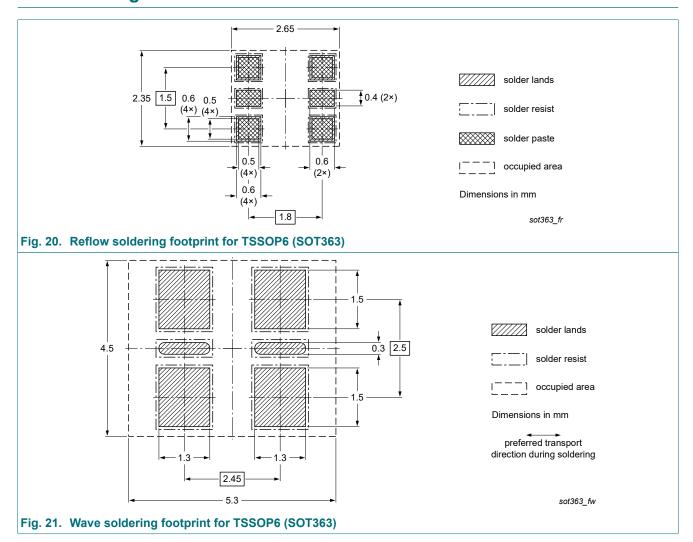
NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

12. Package outline



NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

13. Soldering



NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD10-Q v.1	20210914	Product data sheet	-	-

NPN/PNP double Resistor-Equipped Transistor; R1 = 2.2 k Ω , R2 = 47 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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